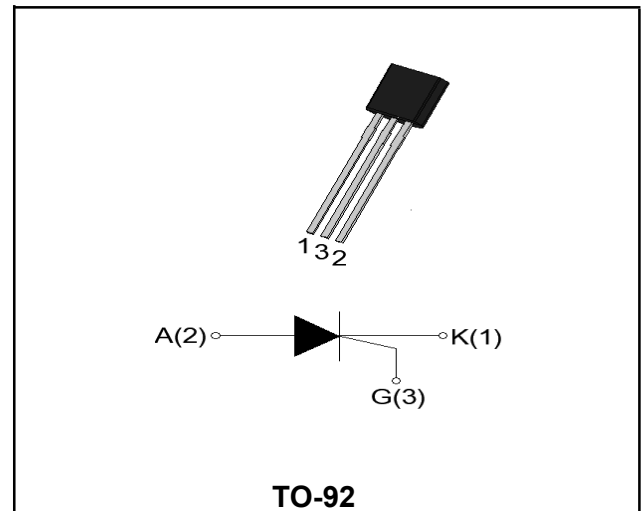


0.8A Sensitive Gate SCRs

Product Summary

Symbol	Value	Unit
$I_{T(AV)}$	0.8	A
$V_{DRM} V_{RRM}$	600/800	V
I_{GT}	10~200	μA



Features

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

Application

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600/800	V
Repetitive peak reverse voltage	V_{RRM}	600/800	V
RMS on-state current	$I_T(RMS)$	0.8	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	8	A
I^2t value for fusing (tp=10ms)	I^2t	0.32	A ² s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di_T/dt	50	A/us
Peak gate current	I_{GM}	0.2	A
Average gate power dissipation	$P_G (AV)$	0.1	W
Junction Temperature	T_J	-40~+110	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value		Unit
			Min	Max	
Gate trigger current	I _{GT}	V _D =12V I _T =10mA T _J =25°C	10	200	uA
Gate trigger voltage	V _{GT}		-	0.8	V
Gate non-trigger voltage	V _{GD}	V _D =1/2V _{DRM} T _J =110°C	0.2	-	V
latching current	I _L	V _D =12V I _G =0.5mA R _{GK} =1kΩ T _J =25°C	-	3	mA
Holding current	I _H		-	4	mA
Critical-rate of rise of commutation voltage	dV _D /dt	V _D =2/3V _{DRM} Gate Open T _J =110°C	10	-	V/us

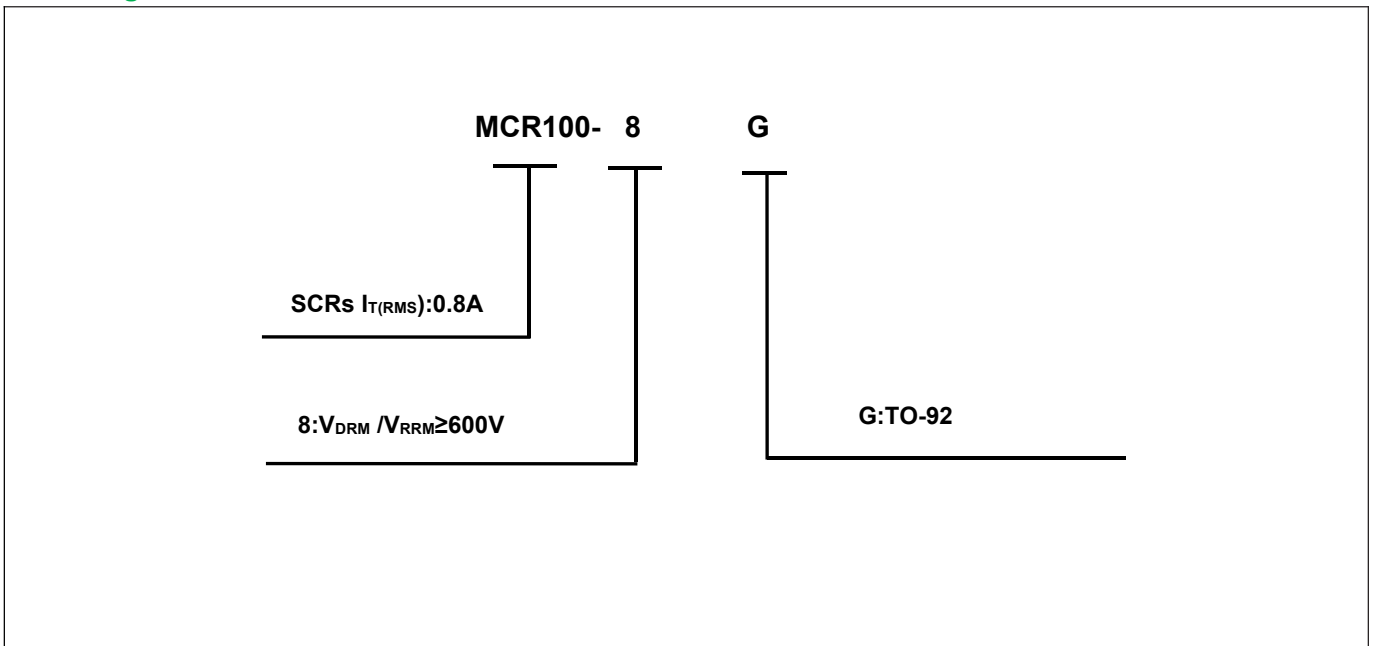
STATIC CHARACTERISTICS

Forward "on" voltage	V _{TM}	I _{TM} =1.2A tp=380us	-	1.55	V	
Repetitive Peak Off-State Current	I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _J =25°C	-	5	uA
Repetitive Peak Reverse Current	I _{RRM}		T _J =110°C	-	0.1	mA

THERMAL RESISTANCES

Thermal resistance	Rth(j-c)	Junction to case(AC)	TYP.	60	°C/W
	Rth(j-a)	Junction to ambient	TYP.	150	°C/W

Ordering Information



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

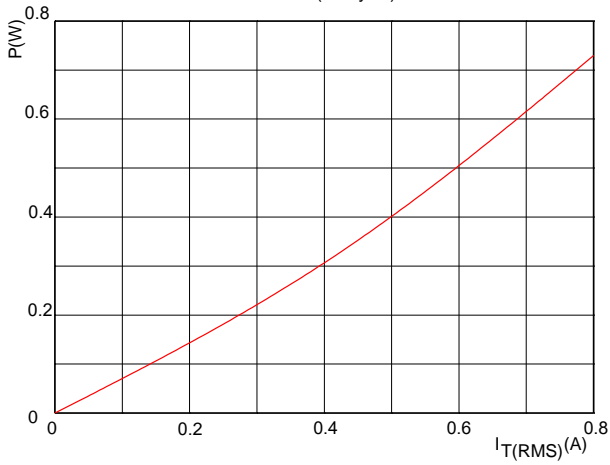


FIG.2: RMS on-state current versus case temperature (full cycle)

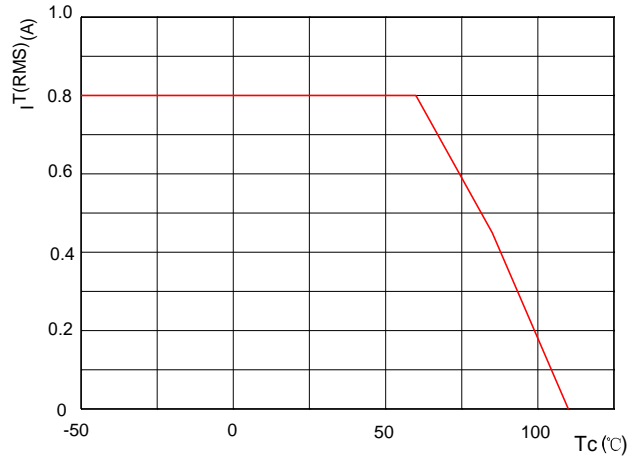


FIG.3: Surge peak on-state current versus number of cycles

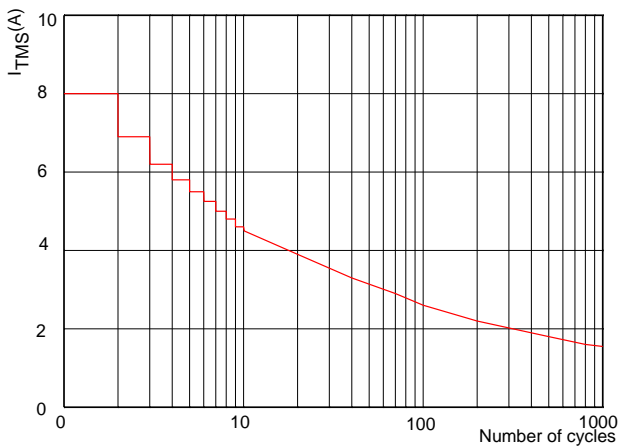


FIG.4: On-state characteristics (maximum values)

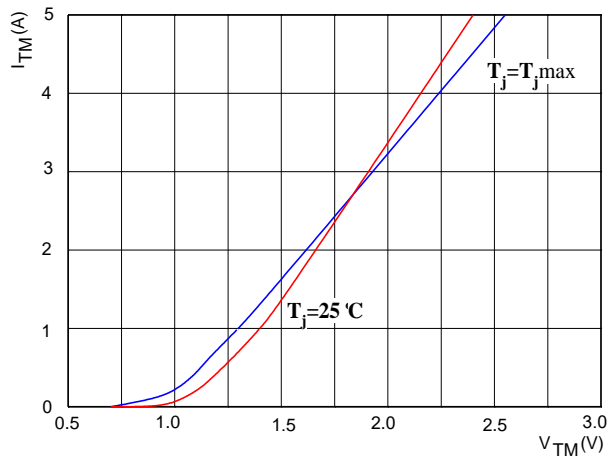


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

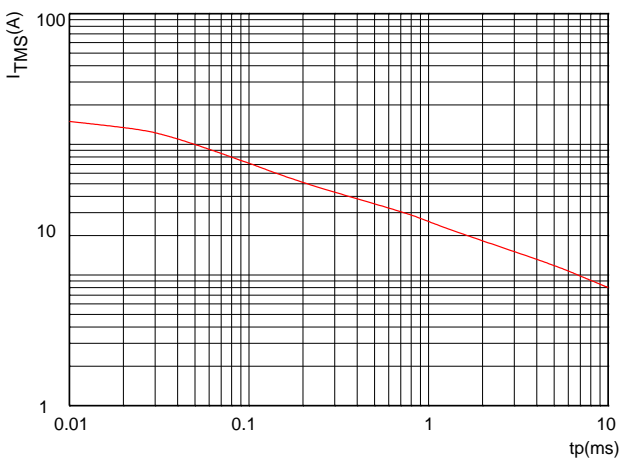
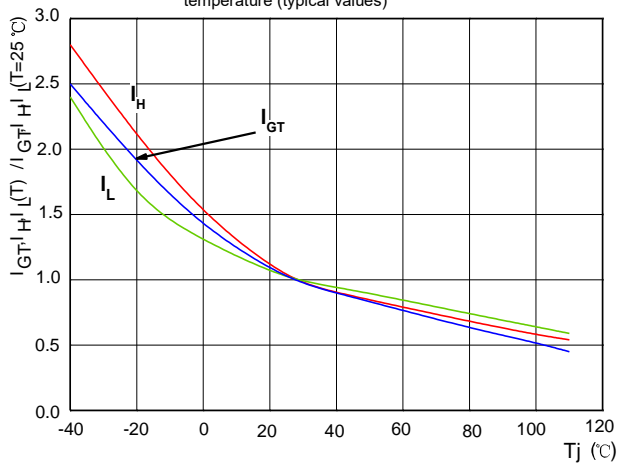


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



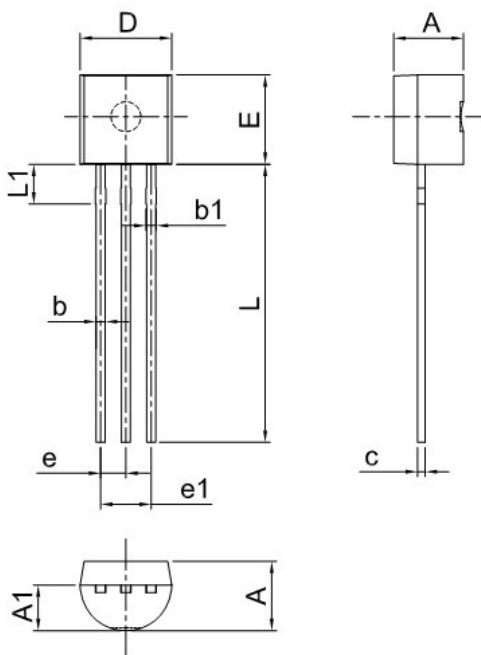
Ordering information

Package	Packing Description	Base Quantity
TO-92	Bulk	1000pcs/Bag
	Tape	2000pcs/Box

Package Dimensions

TO-92

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.70	0.130	0.146
A1	2.30	2.70	0.091	0.106
b	0.40	0.50	0.016	0.020
b1	0.50	0.70	0.020	0.028
c	0.35	0.45	0.014	0.018
D	4.45	4.70	0.175	0.185
E	4.40	4.65	0.173	0.183
e	1.17	1.37	0.046	0.054
e1	2.34	2.64	0.092	0.104
L	13.50	14.50	0.531	0.571
L1	1.80	2.20	0.071	0.087



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